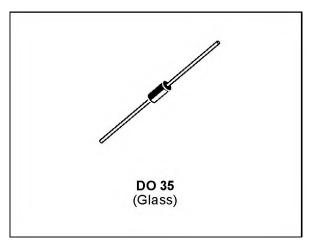


DB3 /DB4 / DC34

TRIGGER DIODES

FEATURES

- VBO: 32V / 34V / 40V VERSIONS
- LOW BREAKOVER CURRENT



DESCRIPTION

High reliability glass passivation insuring parameter stability and protection against junction contamination.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
Р	Power dissipation on printed circuit (L = 10 mm)	Ta = 65 °C	150	mW
I _{TRM}	Repetitive peak on-state current	tp = 20 μs F= 100 Hz	2	А
Tstg Tj	Storage and operating junction temperature range		- 40 to + 125 - 40 to + 125	°C °C

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th (j-a)}	Junction to ambient	400	°C/W
R _{th (j} -I)	Junction-leads	150	°C/W

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Symbol	Parameter	Test Conditions			Value		Unit
				DB3	DC34	DB4	
V _{BO}	Breakover voltage *	C = 22nF ** see diagram 1	MIN	28	30	35	V
			TYP	32	34	40	
			MAX	36	38	45	
[I+V _{BO} I-I-V _{BO} I]	Breakover voltage symmetry	C = 22nF ** see diagram 1	MAX	± 3		V	
ΙΔV± Ι	Dynamic breakover voltage *	∆I = [I _{BO} to I _F =10mA] see diagram 1	MIN	5			V
Vo	Output voltage *	see diagram 2	MIN	5			V
I _{BO}	Breakover current *	C = 22nF **	MAX	100	50	100	μA
tr	Rise time *	see diagram 3	TYP		1.5		μs
IB	Leakage current *	V _B = 0.5 V _{BO} max see diagram 1	MAX	10		μA	

ELECTRICAL CHARACTERISTICS (Tj = 25°C)

* Electrical characteristic applicable in both forward and reverse directions.

** Connected in parallel with the devices.

DIAGRAM 1 : Current-voltage characteristics

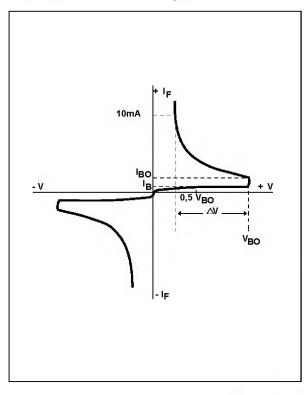
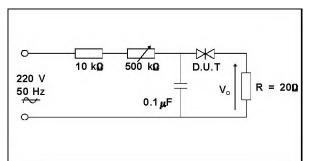
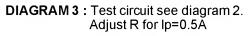
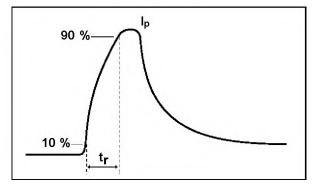


DIAGRAM 2: Test circuit for output voltage









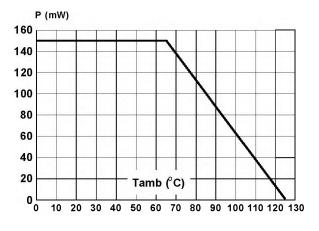


Fig.1 : Power dissipation versus ambient temperature (maximum values)

Fig.2 : Relative variation of V_{BO} versus junction temperature (typical values)

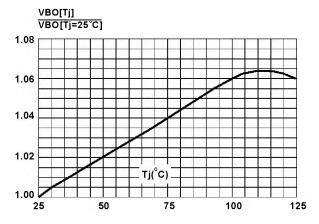
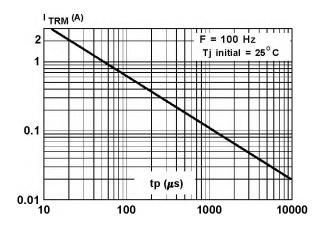


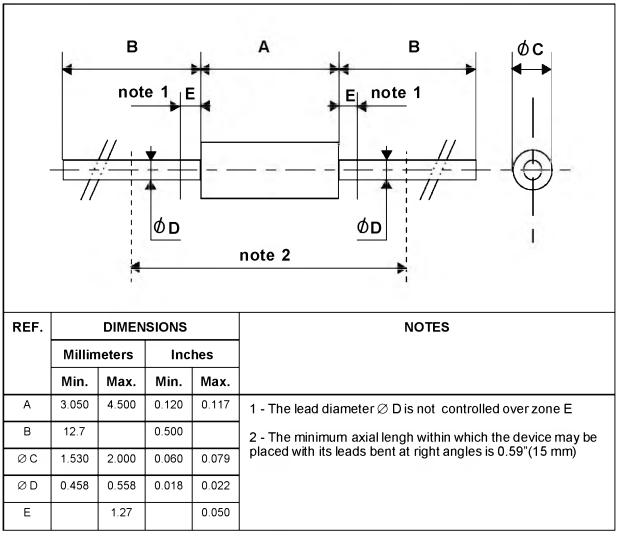
Fig.3 : Peak pulse current versus pulse duration (maximum values)





DB3 / DB4 / DC34

PACKAGE MECHANICAL DATA (in millimeters) DO 35 Glass



Cooling method by convection and conduction Marking : type number Weight : 0.15 g Polarity : N A Stud torque : N A

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